

Thyristor/Diode and Thyristor/Thyristor, 430 A (SUPER MAGN-A-PAK Power Modules)



SUPER MAGN-A-PAK

PRODUCT SUMMARY			
I _{T(AV)}	430 A		
Туре	Modules - Thyristor		
Package	SMAP		
Circuit	Two SCRs doubler circuit		

FEATURES

- · High current capability
- High surge capability
- High voltage ratings up to 2000 V
- 3000 V_{RMS} isolating voltage with non-toxic substrate
- · Industrial standard package
- UL approved file E78996
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- Motor starters
- DC motor controls AC motor controls
- Uninterruptible power supplies
- Wind mill

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
1		430	A		
I _{T(AV)}	T _C	82	°C		
1		675	A		
I _{T(RMS)}	T _C	82	°C		
1	50 Hz	15.7	kA		
ITSM	60 Hz	16.4	KA		
l ² t	50 Hz	1232	kA ² s		
141	60 Hz	1125	KA-S		
I ² √t		12 320	kA²√s		
V _{RRM}	Range	1600 to 2000	V		
T _J	Range	- 40 to 150	°C		
T _{Stg}	Range	- 40 to 130			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM}/I_{DRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA			
	16	1600	1700				
VSK.430	18	1800	1900	100			
	20	2000	2100				

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ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	I _{T(AV),}	180° conduction, half sine wave			430	А
at case temperature	I _{F(AV)}	100 Condu	Clion, nan sine v	vave	82	°C
Maximum RMS on-state current	I _{T(RMS)}	180° condu	ction, half sine v	vave at T _C = 82 °C	675	Α
		t = 10 ms	No voltage		15.7	kA
Maximum peak, one-cycle,	I _{TSM,}	t = 8.3 ms	reapplied		16.4	
non-repetitive surge current	I _{FSM}	t = 10 ms	100 % V _{RRM}		13.2	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	13.8	
	l ² t	t = 10 ms	No voltage	initial $T_J = T_J$ maximum	1232	- kA ² s
Maximum 124 for fusing		t = 8.3 ms	reapplied		1125	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		871	
		t = 8.3 ms	reapplied		795	
Maximum I²√t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied		12 320	kA²√s	
Low level value of threshold voltage	V _{F(TO)1}	(16.7 % x π x I _{T(AV)} < I < π x I _{T(AV)}), T _J = T _J maximum		0.96	V	
High level value of threshold voltage	V _{F(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.06	V	
Low level value of on-state slope resistance	r _{f1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		0.51		
High level value of on-state slope resistance	r _{f2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		0.45	mΩ	
Maximum on-state voltage drop	V_{TM}	I_{pk} = 1500 A, T_J = 25 °C, t_p = 10 ms sine pulse		1.65	V	
Maximum forward voltage drop	V_{FM}	I_{pk} = 1500 A, T_J = 25 °C, t_p = 10 ms sine pulse		1.65	V	
Maximum holding current	I _H	T 05 00 and a set 40 V set till a land		500	mA	
Typical latching current	IL	T _J = 25 °C, anode supply 12 V resistive load		1000	IIIA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum rate of rise of turned-on current	dl/dt	$T_J = T_J$ maximum, $I_{TM} = 400$ A, V_{DRM} applied	1000	A/µs	
Typical delay time	t _d	Gate current 1 A, $dI_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	2.0		
Typical turn-off time	t _q	I_{TM} = 750 A, T_J = T_J maximum, dI/dt = - 60 A/μs V_R = 50, dV/dt = 20 V/μs, Gate 0 V 100 Ω	200	μs	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 130$ °C, linear to $V_D = 80$ % V_{DRM}	1000	V/µs
RMS insulation voltage	V _{INS}	t = 1 s	3000	V
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	TJ		- 40 to 130	°C
Maximum storage temperature range	T _{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case per junction	R _{thJC}	DC operation	0.065	K/W
Maximum thermal resistance, case to heatsink	R _{thC-hs}		0.02	FC/VV
SMAP to heatsin	k	A mounting compound is recommended and	6 to 8	
Mounting torque ± 10 % busbar to SMA	P	the torque should be rechecked after a period of 3 hours to allow for the spread of the compound.	12 to 15	Nm
Approximate weight			1500	g
Case style		See dimensions - link at the end of datasheet	SUPER MA	GN-A-PAK

△R _{thJC} CONDUCTION					
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS	
180°	0.009	0.006			
120°	0.011	0.011			
90°	0.014	0.015	$T_J = T_J$ maximum	K/W	
60°	0.021	0.022			
30°	0.037	0.038			

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

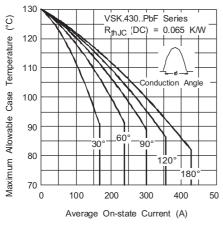


Fig. 1 - Current Ratings Characteristics

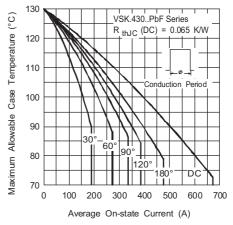


Fig. 2 - Current Ratings Characteristics



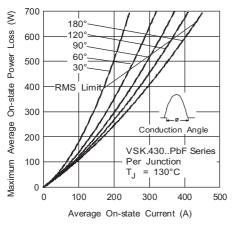


Fig. 3 - On-State Power Loss Characteristics

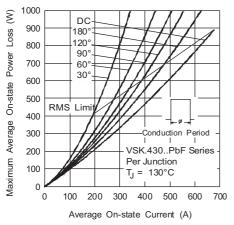


Fig. 4 - On-State Power Loss Characteristics

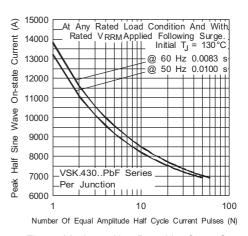


Fig. 5 - Maximum Non-Repetitive Surge Current

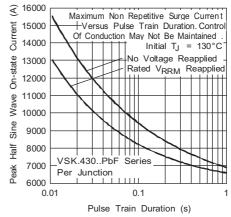


Fig. 6 - Maximum Non-Repetitive Surge Current

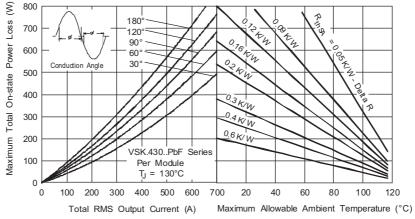


Fig. 7 - On-State Power Loss Characteristics

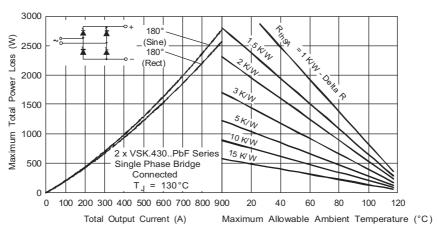


Fig. 8 - On-State Power Loss Characteristics

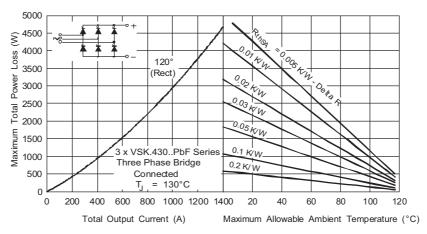


Fig. 9 - On-State Power Loss Characteristics

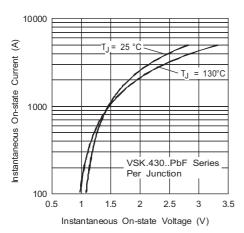


Fig. 10 - On-State Voltage Drop Characteristics

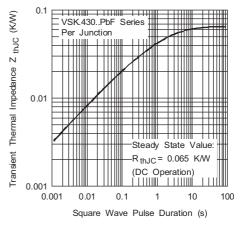


Fig. 11 - Thermal Impedance Z_{thJC} Characteristics

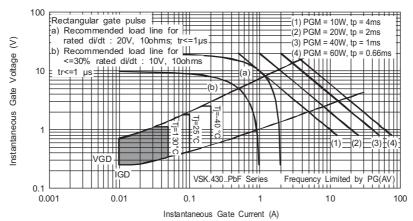
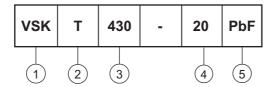


Fig. 12 - Gate Characteristics

ORDERING INFORMATION TABLE



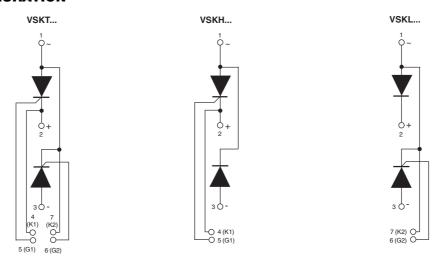


- 1 Module type
- Circuit configuration (see end of datasheet)
- Current rating
- Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 5 Lead (Pb)-free

Note

• To order the optional hardware go to www.vishay.com/doc?95172

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95283		

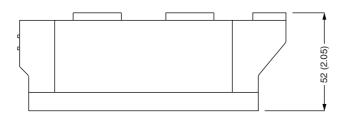
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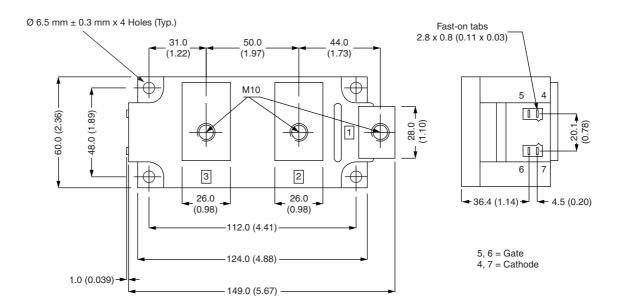




Super MAGN-A-PAK Thyristor/Diode

DIMENSIONS in millimeters (inches)





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